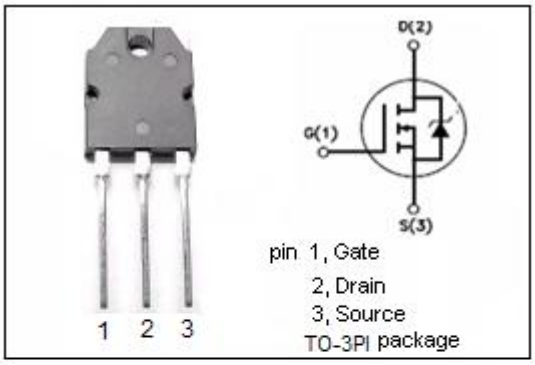
isc N-Channel MOSFET Transistor 2SK400

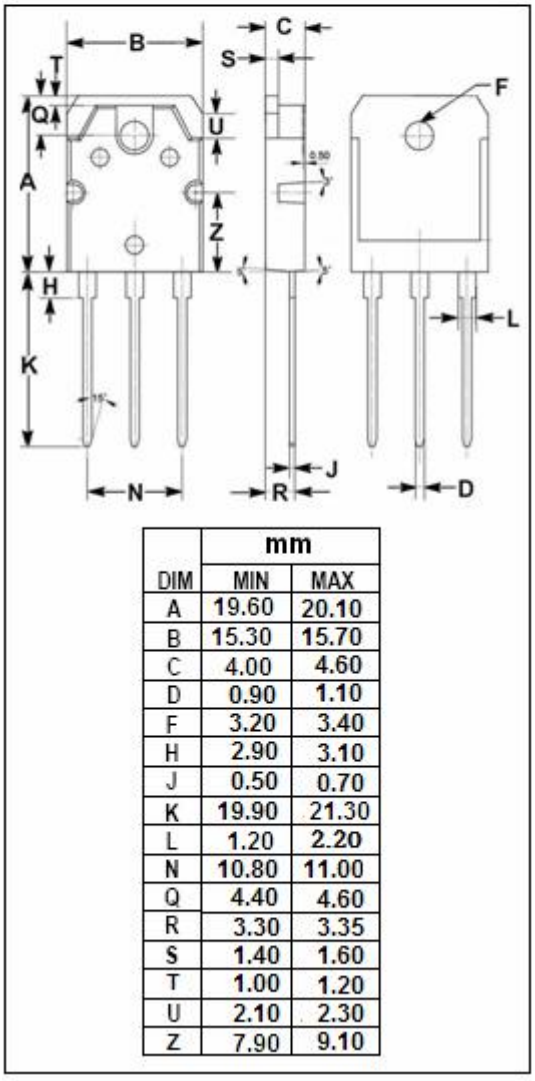


DESCRIPTION

- Drain Current –I_D=8A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}=200V(Min)
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- low on–resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switchingregulator, DC–DC convertor



DIM	mm MIN	mm MAX
A	19.60	20.10
B	15.30	15.70
C	4.00	4.60
D	0.90	1.10
F	3.20	3.40
H	2.90	3.10
J	0.50	0.70
K	19.90	21.30
L	1.20	2.20
N	10.80	11.00
Q	4.40	4.60
R	3.30	3.35
S	1.40	1.60
T	1.00	1.20
U	2.10	2.30
Z	7.90	9.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	200	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ TC=25℃	8	A
P_{tot}	Total Dissipation@TC=25℃	100	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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• ELECTRICAL CHARACTERISTICS (T_C=25℃)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0; I_D= 10mA	200			V
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}= 10V; I_D= 1mA	2.0		5.0	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	V_{GS}= 15V; I_D=4A		0.5	0.7	Ω
V_{SD}	Drain Forward Voltage	I_F=4A; V_{GS}=0		0.9		V
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±20V; V_{DS}= 0			±1	uA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=160V; V_{GS}= 0			1	mA